

ABSTRACT

MASK BLANK, METHOD FOR MANUFACTURING TRANSFER MASK, AND
METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

In the present invention, an etching stopper film (2), a light-blocking film (3) comprising a material containing one or more elements selected from among silicon and tantalum, and a hard mask film (4) are laminated in that order on a translucent substrate (1). The etching stopper film is made of a material containing chromium, oxygen and carbon, the chromium content is 50 atom% or more, the maximum peak in a N1s narrow spectrum obtained by means of analysis using X-Ray photoelectron spectroscopy is below the detection limit, and a Cr2p narrow spectrum obtained by means of analysis using X-Ray photoelectron spectroscopy has a maximum peak at a bond energy of 574 eV or less.

FIG. 1